

A 115mW CMOS GPS Receiver

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OUTLINE

- **GPS Overview / Receiver Architecture**
- Low-Noise Amplifiers
 - CMOS noise models.
 - Power-constrained optimization.
- Active $G_m - C$ Filters
 - Dynamic range analysis.
 - Power-efficient transconductor design.
- CMOS GPS Receiver Implementation
- Experimental Results
- Summary and Contributions

GPS OVERVIEW: WHY RF CMOS?

- CMOS enjoys the benefits of aggressive scaling, driven by the microprocessor industry.
- Economies of scale. We want to be a barnacle on the Intel whale.
- Future co-integration of baseband (DSP).
- If it *can* be done competitively in CMOS, it will.

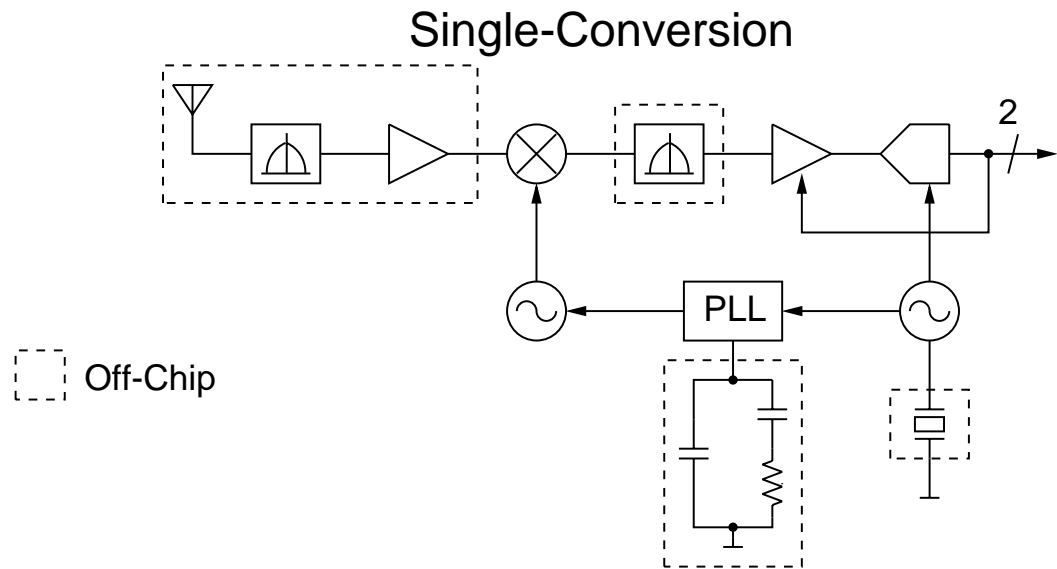
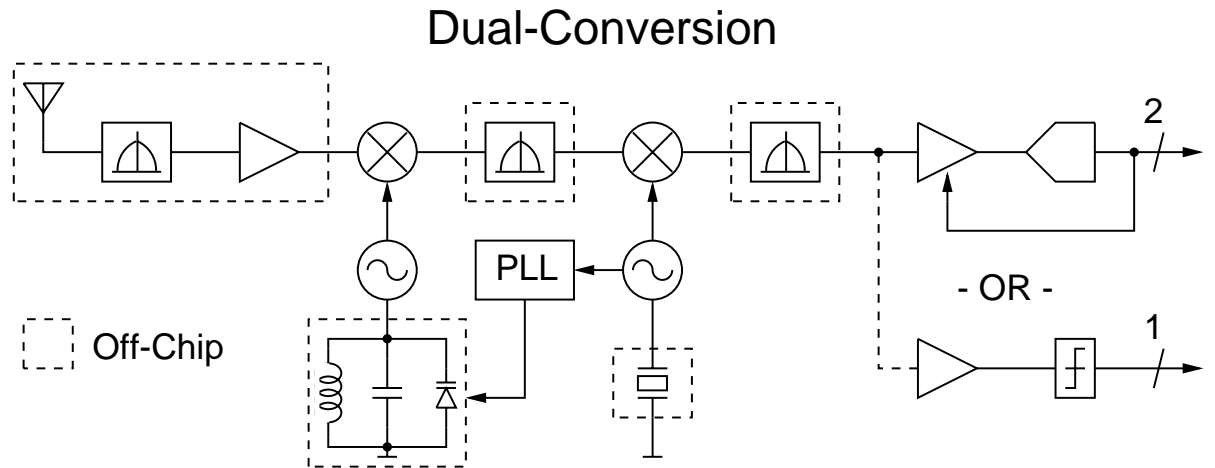
GPS OVERVIEW: THE SYSTEM

- 24 satellites in LEO, broadcasting their position and local time.
- With 4 satellites in view, can use one-way ranging to solve for x, y, z, t .
- Consumer applications: automotive navigation, smart cellular handoff, cellular emergency (911) dispatch, smart clocks.
- For wide proliferation, need receivers to be cheap, compact (single-chip), low-power and easy to use.

GPS OVERVIEW: TYPICAL RECEIVER ARCHITECTURES

Distinguishing Features:

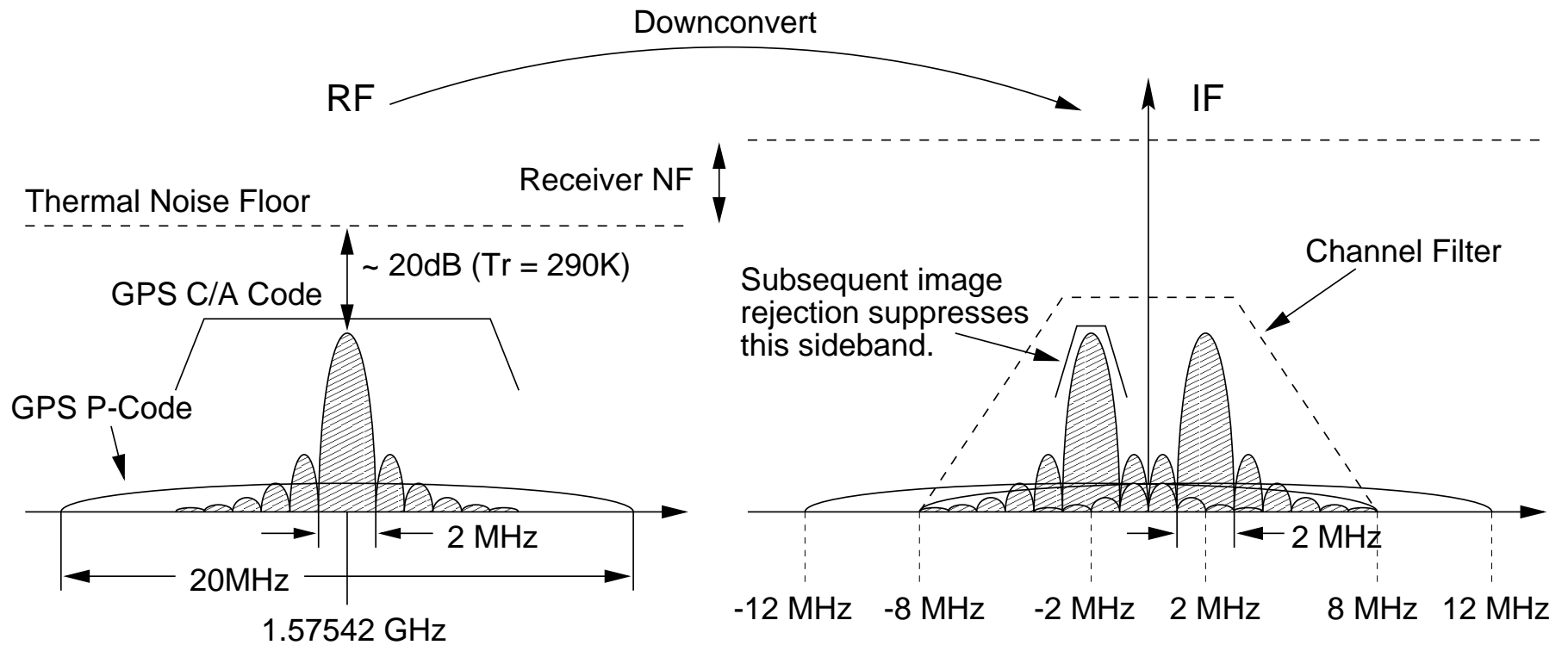
- Typical on-chip P_D is 100mW – 500mW
- Off-chip LNA or active antenna
- Off-chip IF filtering
- 1 or 2 bit quantization



GPS OVERVIEW: TYPICAL RECEIVER SPECIFICATIONS

Spec	Sony (JSSC Apr'97)	GEC PIsy. GP2010	SiRF GRF-1
LNA NF	2dB (ext)	≈ 2dB (ext)	(ext)
Chip NF	6.1dB	≈ 10dB	—
IIP3	-14.5dBm	—	—
P-1dB	-29dBm	—	—
Total Gain	107dB	106dB	—
ADC	1-bit	2-bit	2-bit
Power	81mW @ 3V	200mW @ 3V	500mW @ 5V
Technology	15GHz Bipolar	Bipolar	—
Missing	2 Filters LNA, PLL LF	2 Filters, LNA, PLL LF	Filter, LNA

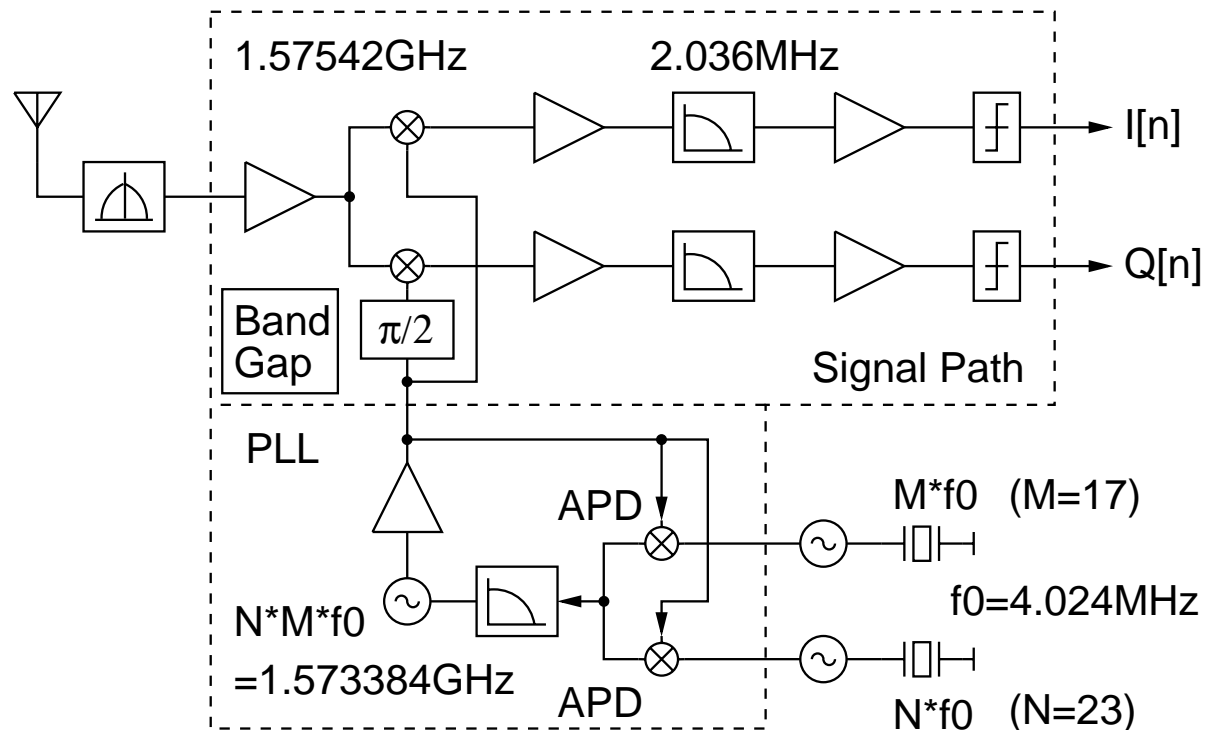
GPS OVERVIEW: SIGNAL STRUCTURE



ARCHITECTURE: LOW-IF RECEIVER

Primary Goal: Make choices to minimize P_D , maximize integration.

- Low-IF \Rightarrow On-chip active channel filter.
- Image in GPS band \Rightarrow Relaxed I/Q matching.
- Eliminate PLL prescaler \Rightarrow Saves power / noise.
- 1-bit quantization for simplicity.

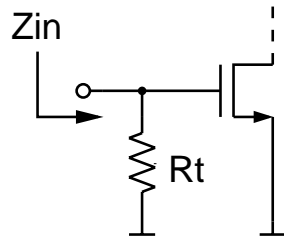


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LNA: HOW TO GET 50Ω

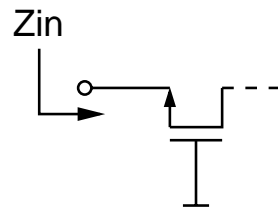
Several Common Techniques



Resistive Termination

$$Z_{in} = R_t$$

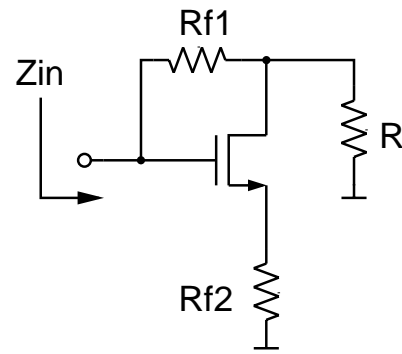
Great termination.
Poor NF.



g_m Termination

$$Z_{in} = \frac{1}{g_m}$$

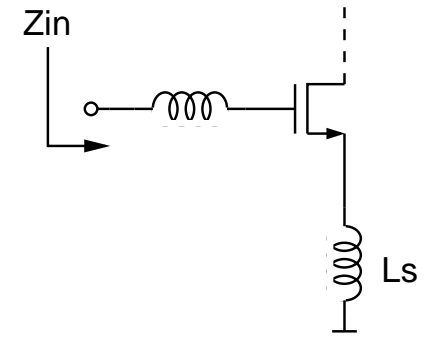
NF > 3dB
($\gamma > 1$)



Dual Feedback

$$Z_{in} = \sqrt{R_{f1} R_{f2}}$$

Broadband.
High power dissipation.

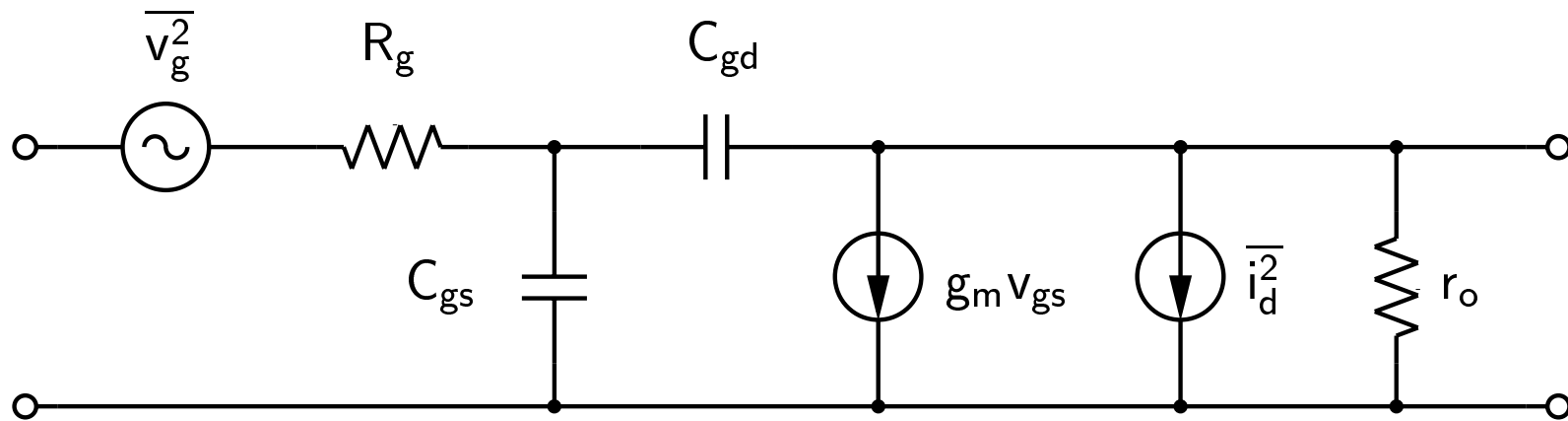


Inductive Degeneration

$$\text{Re}[Z_{in}] = \frac{g_m L_s}{C_{gs}}$$

Narrowband.
Best NF.

LNA: STANDARD CMOS NOISE MODEL

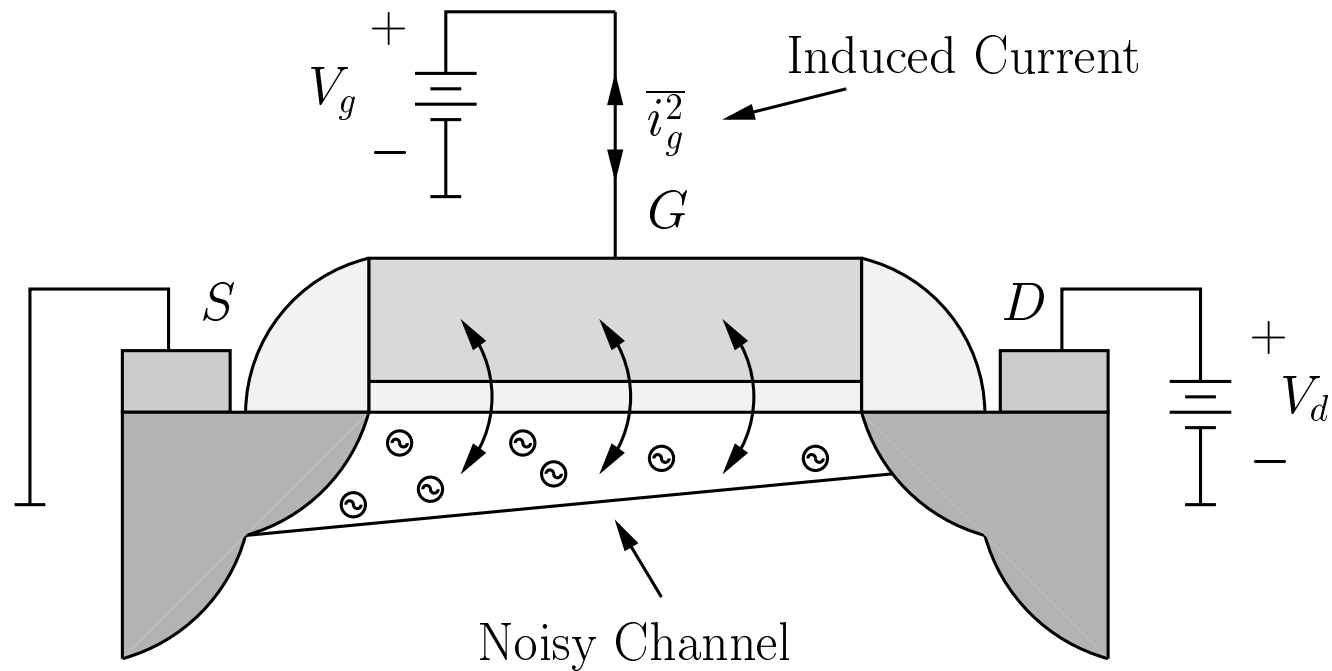


- Channel thermal noise is the dominant source of noise.

$$\overline{i_d^2} = 4kTB\gamma g_{d0}$$

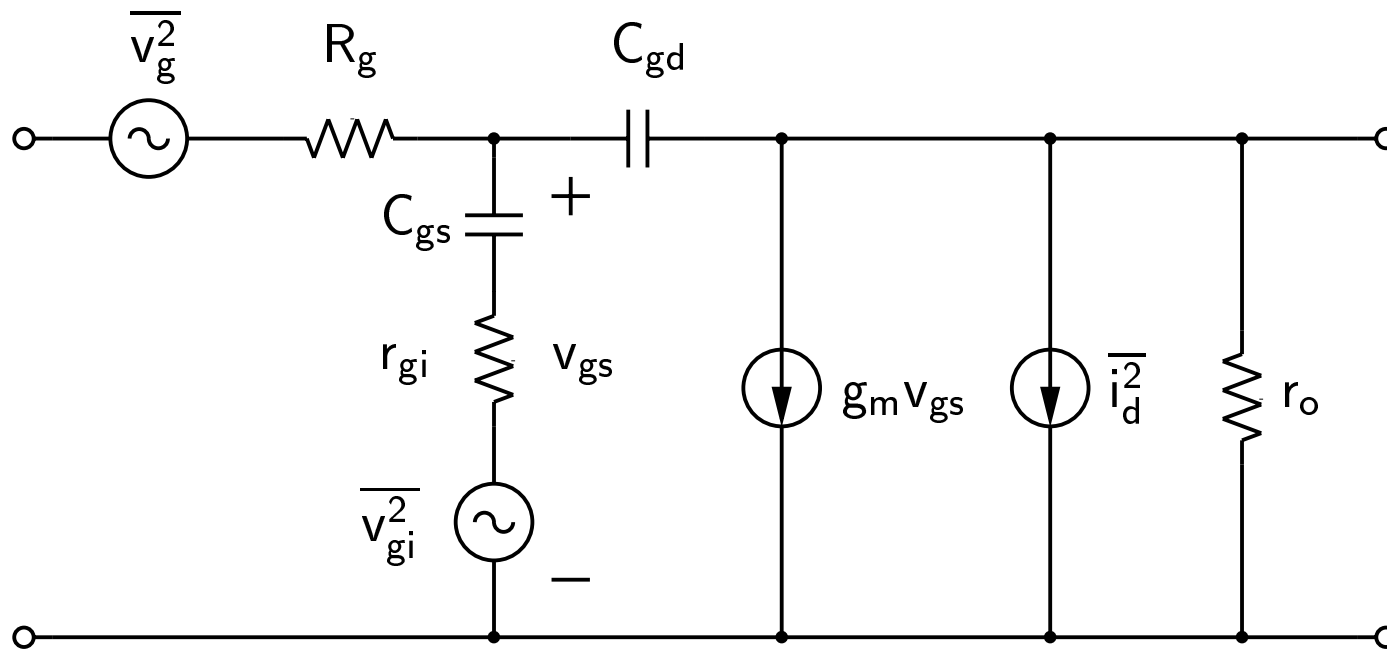
- Gate resistance noise can be minimized by good layout.
- Problem: Yields $F_{min} = 0$ dB!

LNA: INDUCED GATE EFFECTS



- Gate noise current. $\overline{i_g^2} = 4kTB\delta \frac{(\omega C_{gs})^2}{5g_{d0}}$
- Real component of Y_g . $\text{Re}[Y_g] = \frac{(\omega C_{gs})^2}{5g_{d0}}$

LNA: REVISED CMOS NOISE MODEL



$$\overline{v_{gi}^2} = 4kTB\delta r_{gi}$$

$$r_{gi} = \frac{1}{5g_{d0}}$$

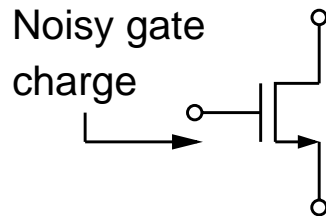
(Note the placement of v_{gs} .)

LNA: INDUCED GATE NOISE MODELS

Induced gate noise is not included in standard CMOS simulation models!
(Exceptions: Philips MOS9, Tektronix BSIM3)

How do we get around this?

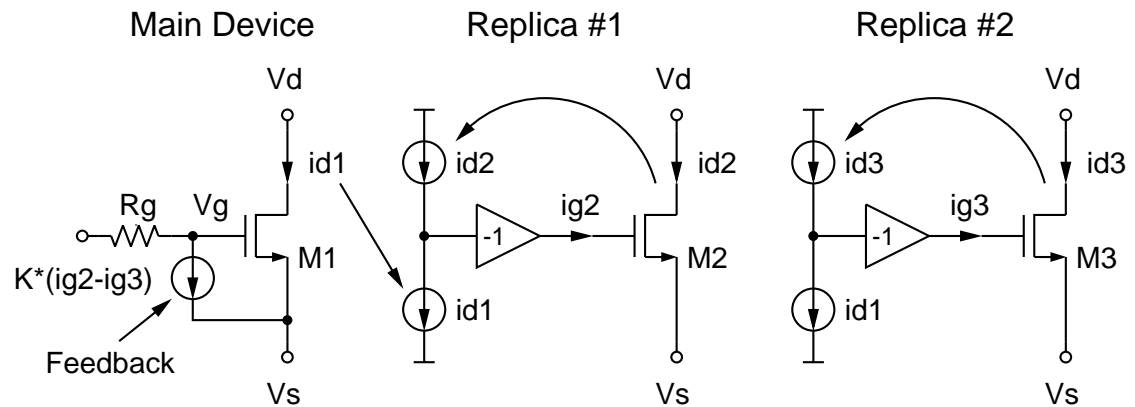
Charge Model



$$\overline{Q_g^2} = 4kTB\delta \frac{C_{gs}^2}{5g_{d0}}$$

Modify simulation code.

Macro Model



Can be used with any simulator/model.

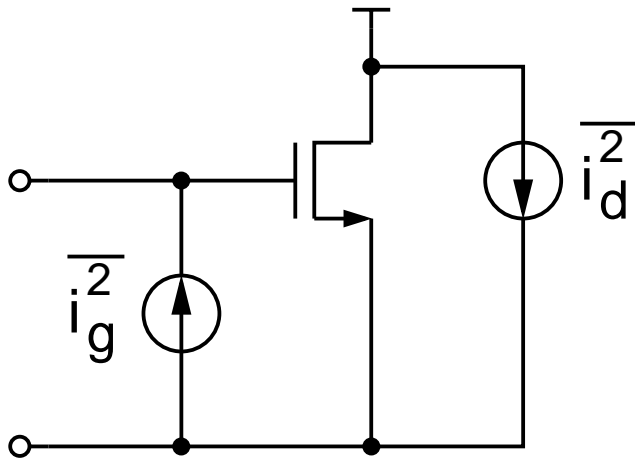
LNA: OPTIMIZING NF

Two approaches:

- Classical: Assume a *fixed* small-signal model for the device. Optimize the source impedance for minimum noise factor. (Haus et al. 1960)
Problem - Ignores input match, power gain.
- Power-constrained: Assume conditions for input impedance match. Fix P_D and vary the device width for minimum noise factor. (Shaeffer, Lee 1997)

LNA: CLASSICAL F_{min}

The minimum noise figure can be calculated for the MOSFET according to the classical two-port approach, once the induced gate noise is included.

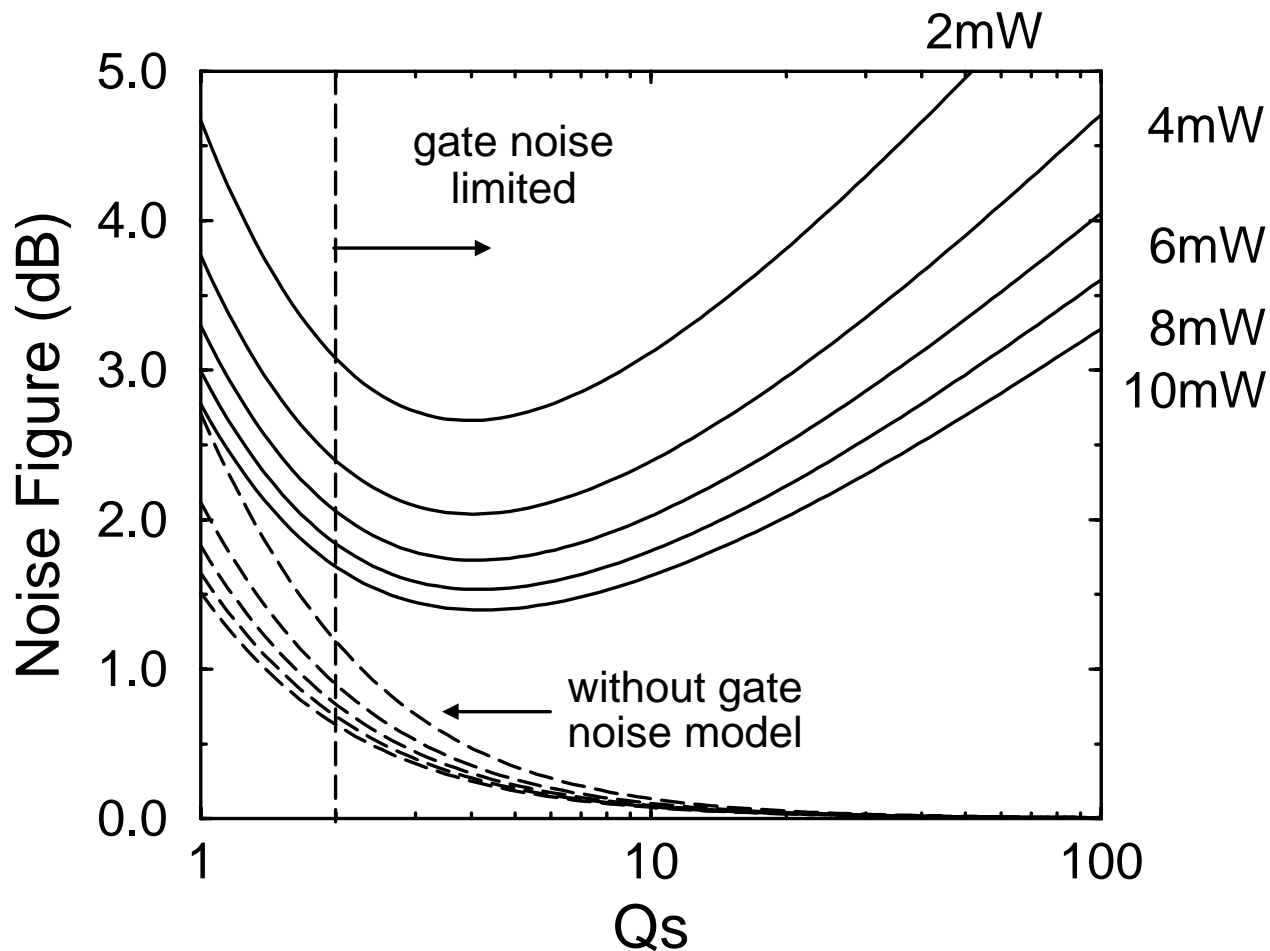


$$F_{min} = 1 + \sqrt{\frac{4}{5} \delta \gamma (1 - |c|^2)} \left(\frac{\omega_0}{\omega_T} \right)$$

$$Q_{opt} = \left| \frac{B_{opt}}{G_{opt}} \right| = \frac{\sqrt{\frac{5\gamma}{\delta \alpha^2} + |c|}}{\sqrt{1 - |c|^2}} \approx 2.162$$

H.A. Haus et al., "Representation of noise in linear twoports," Proc. of the IRE, January 1960.

LNA: POWER CONSTRAINED OPTIMIZATION



Assumptions

- $L_{eff} = 0.44\mu m$
- $\gamma = 1.3, \delta = 2.6$
- $V_{DD} = 2.5V$
- $f_0 = 1.6GHz$
- $R_s = 50\Omega$

Result: $Q_{opt} \approx 3.5$

LNA: POWER CONSTRAINED OPTIMIZATION

Power-constrained optimization yields a design with:

- Lowest NF for a given P_D

$$\frac{F_{min, P_D}^{-1}}{F_{min}^{-1}} = 0.763$$

- Input impedance match.
- Higher G_m than the classical method.
- Higher current densities than the classical method.

Rule of thumb: $W_{opt} f_0 \approx 500 \mu m \cdot \text{GHz}$.

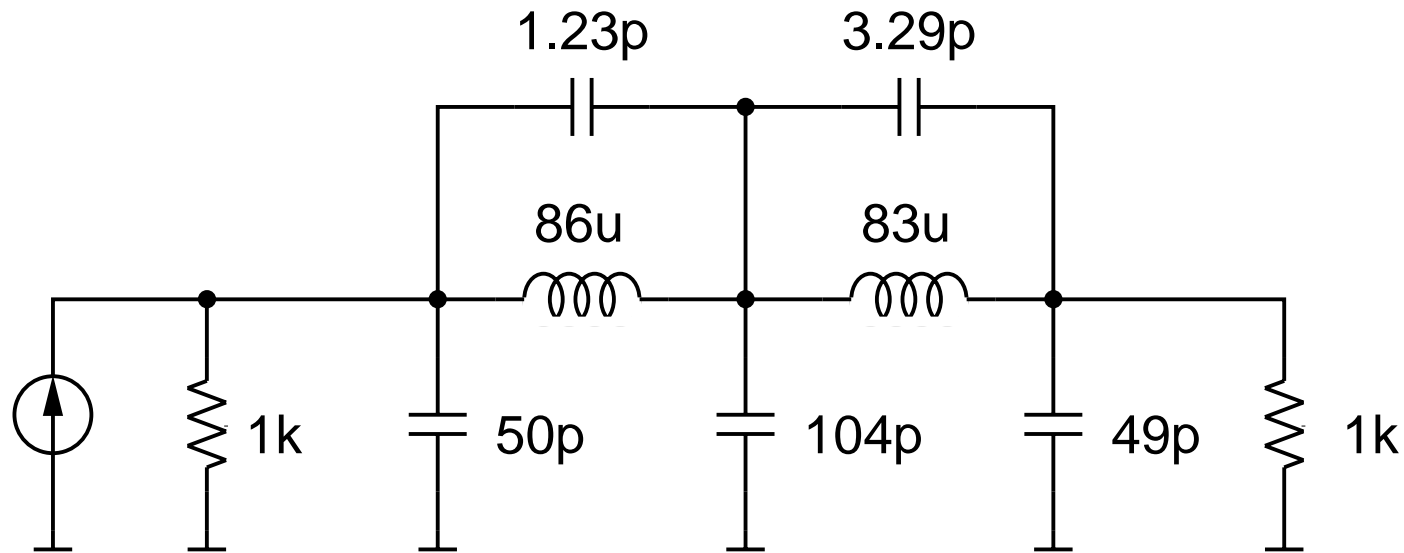
LNA: SUMMARY

- CMOS noise models are currently insufficient for design.
 - Modeling of hot electron effects.
 - Modeling of the induced gate noise.
- Power-constrained noise optimization technique permits:
 - Optimized noise performance.
 - Simultaneous input impedance matching.
 - Maximum LNA gain.
- Results: 2.4dB NF, 1.6GHz, 12mW, differential LNA in a 0.5 μ m CMOS technology. (6mW single-ended equivalent.)

OUTLINE

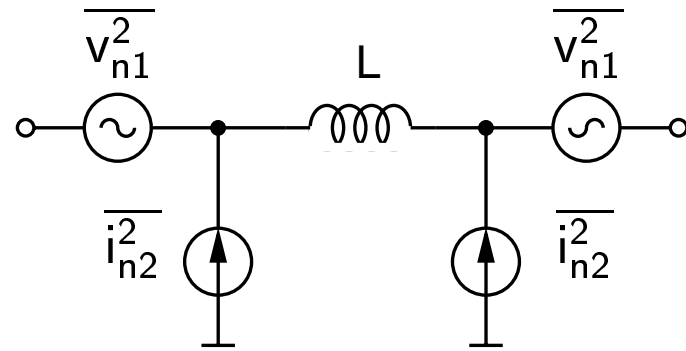
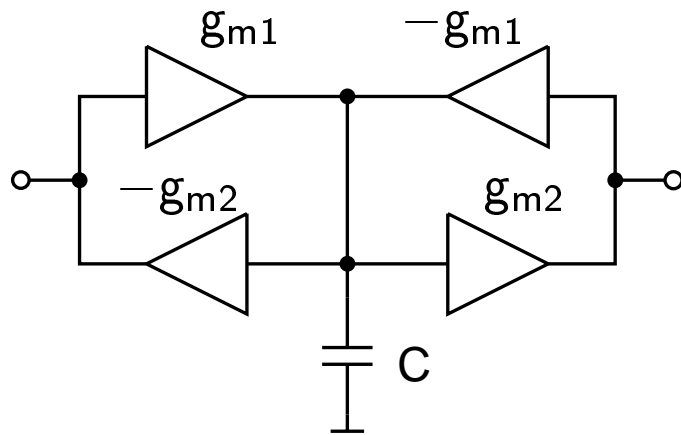
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FILTER: ARCHITECTURE



- 5th-order elliptical lowpass filter.
- 3MHz bandwidth, 77dB stopband rejection.
- Inductors are impractical for integration.

FILTER: GYRATOR



$$L = \frac{C}{g_{m1} g_{m2}}$$

- A gyrator implements an active inductor.
- Noise, distortion limit the gyrator's utility.

FILTER: DESIGN APPROACH

The filter is the most critical signal path element, and therefore requires the most attention to detail. Some relevant ideas:

- Interesting fact: $F_{min} = 2(1 + \epsilon N)$. Independent of filter Z_0 !
This implies a fixed amount of *power gain* to suppress filter noise.
- Fixed $G_P \Rightarrow A_V \propto \sqrt{Z_0}$.
Need to minimize Z_0 to maximize dynamic range.
- Seek linearization techniques that maximize G_m / I_{bias} .
One sub-optimal approach would be linearization by degeneration.
- Use Class-AB techniques, if possible, to maximize power efficiency.

In short: *It all depends on the transconductor!*

FILTER: MAXIMIZING DYNAMIC RANGE

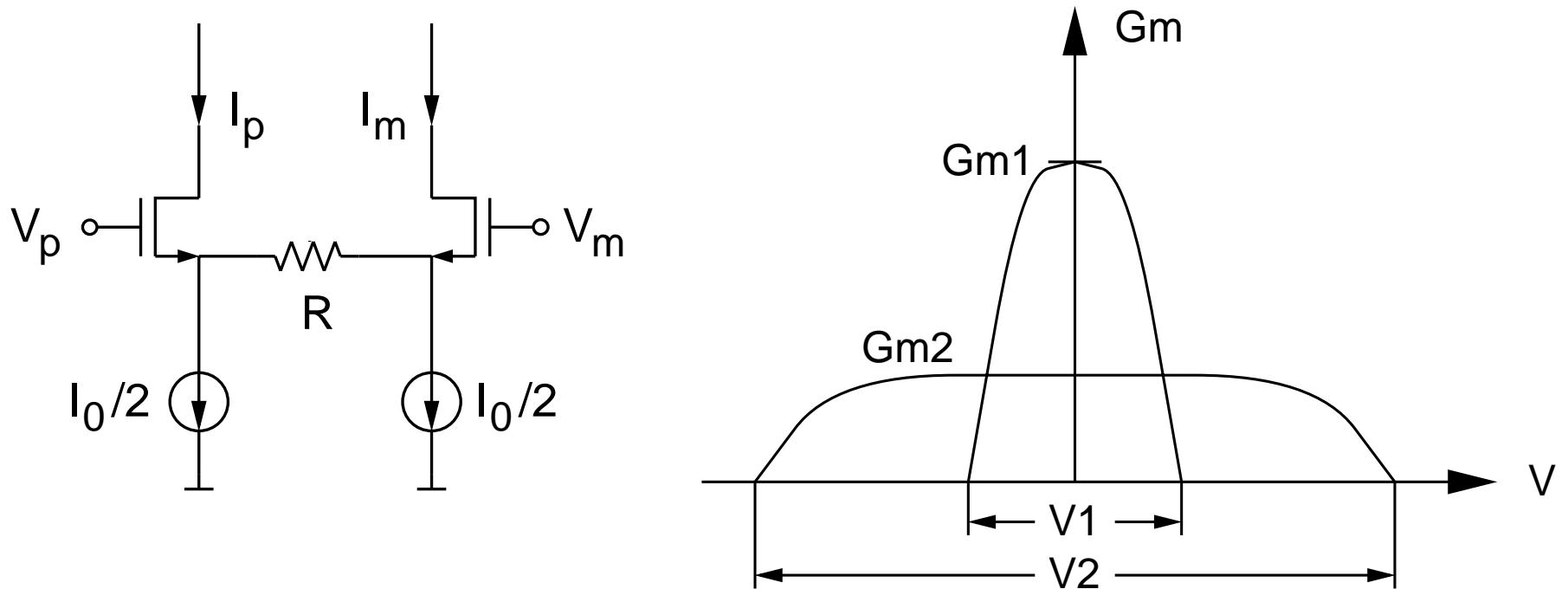
- Filter architecture.
 - Minimize Q and order of the filter.
 - Maximize transition bandwidth.
- Transconductor architecture.

$$\text{Transconductor F.O.M. : } \Gamma_m = \frac{\beta V_{IP3}^2}{\epsilon}$$

β	G_m/P_D .
V_{IP3}^2	Voltage IIP3.
ϵ	Noise factor.

FILTER: PROBLEMS WITH CLASS-A

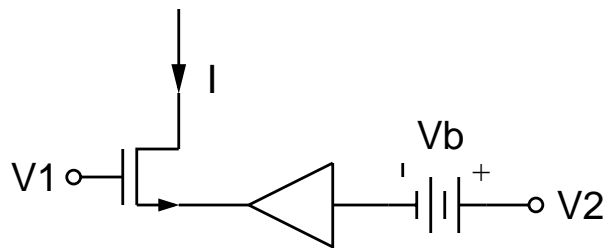
Class-A transconductors trade G_m for linearity.



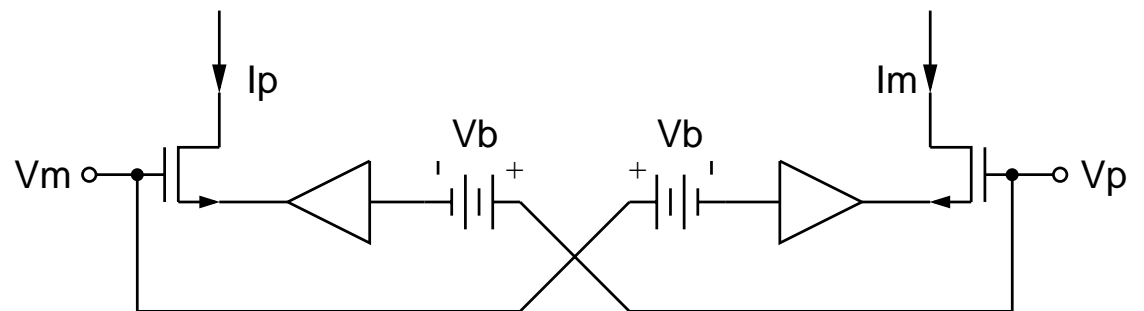
$$G_{m1} V_1 = G_{m2} V_2 \propto I_0$$

FILTER: A SQUARE-LAW TRANSCONDUCTOR.

Square-law
half transconductor.



Linear full transconductor.

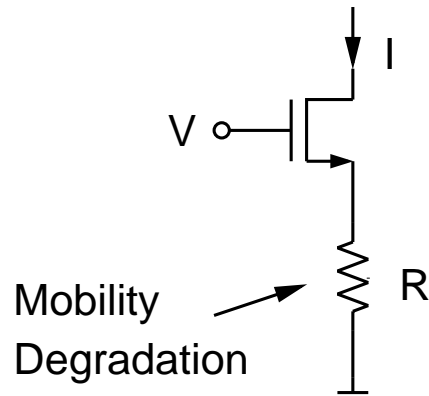


Problems:

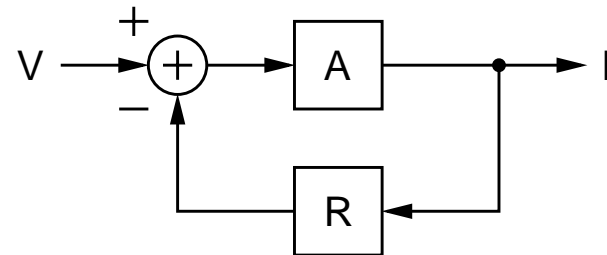
- Velocity saturation. \rightarrow Use longer L .
- Vertical-field mobility degradation.

FILTER: MOBILITY DEGRADATION

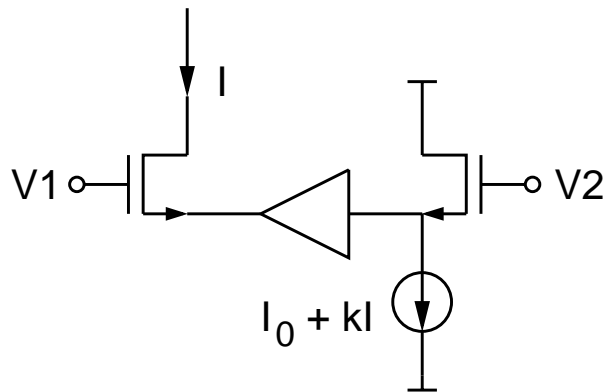
Equivalent circuit.



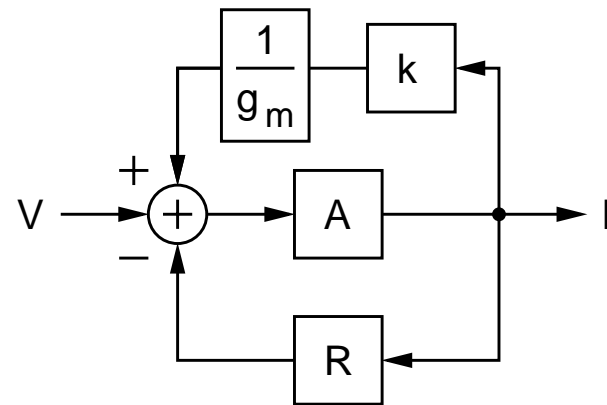
Equivalent system.



With PFB.

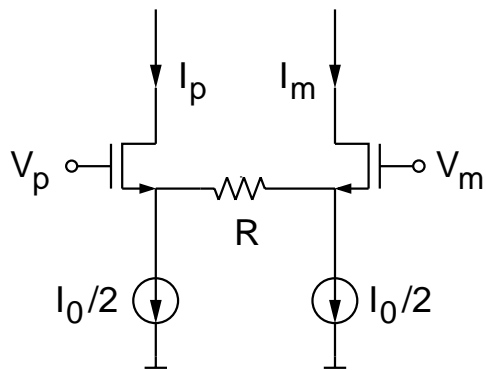


With PFB.

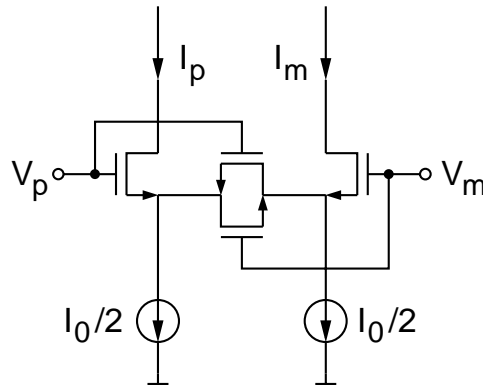


FILTER: TRANSCONDUCTOR SURVEY

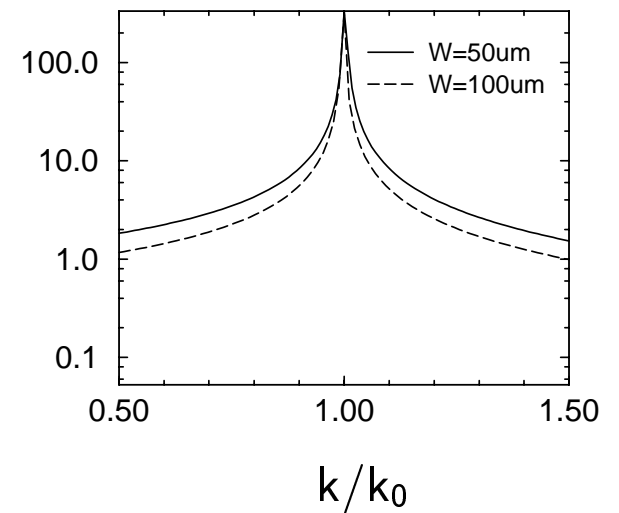
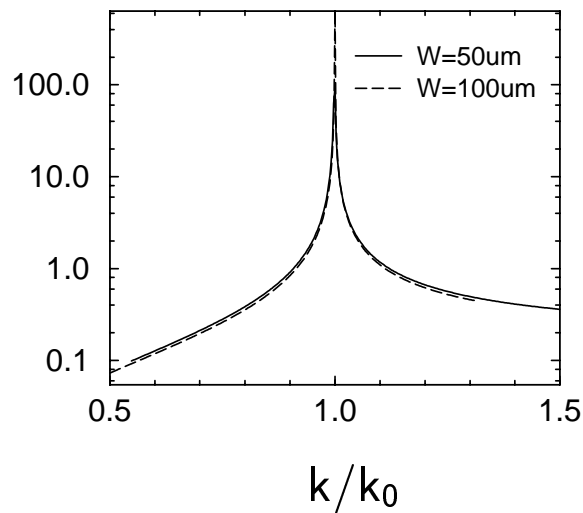
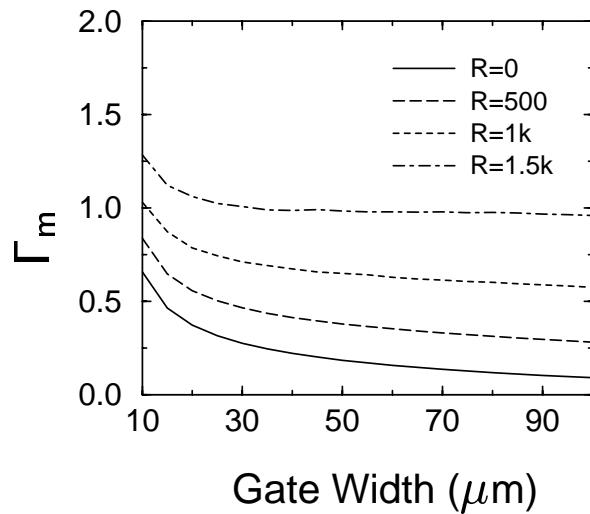
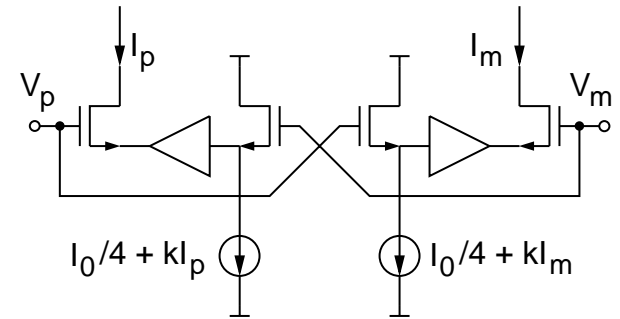
Differential Pair



MOS-Degenerated Pair



PFB Pair



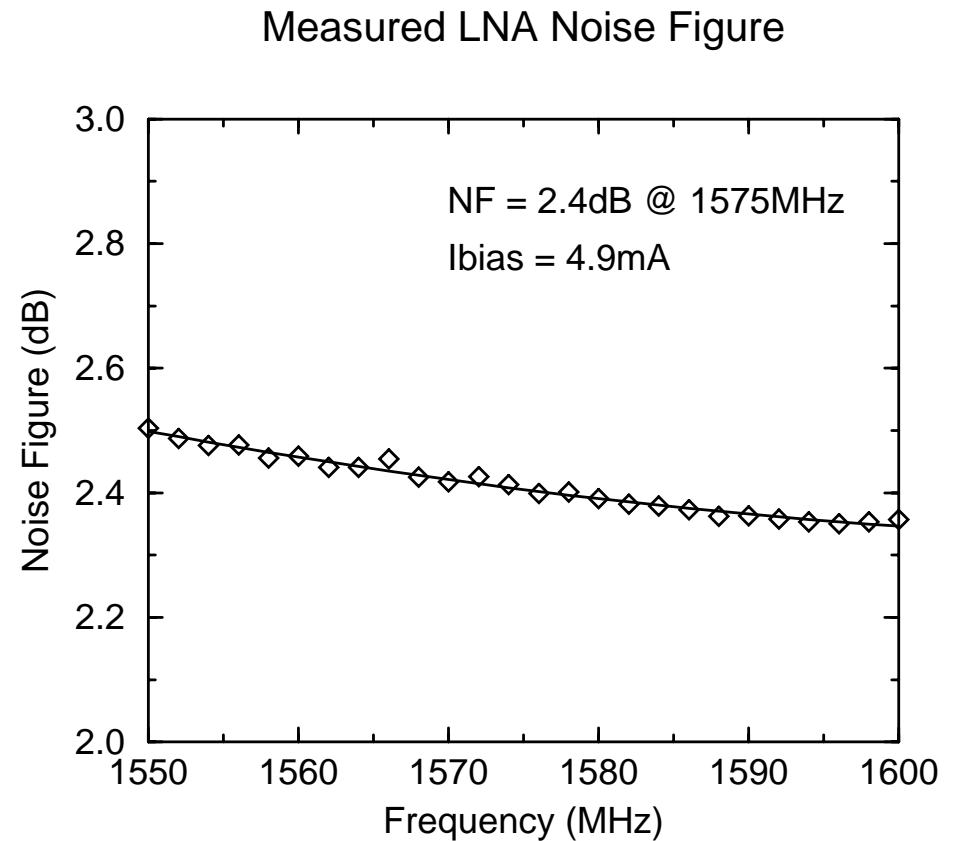
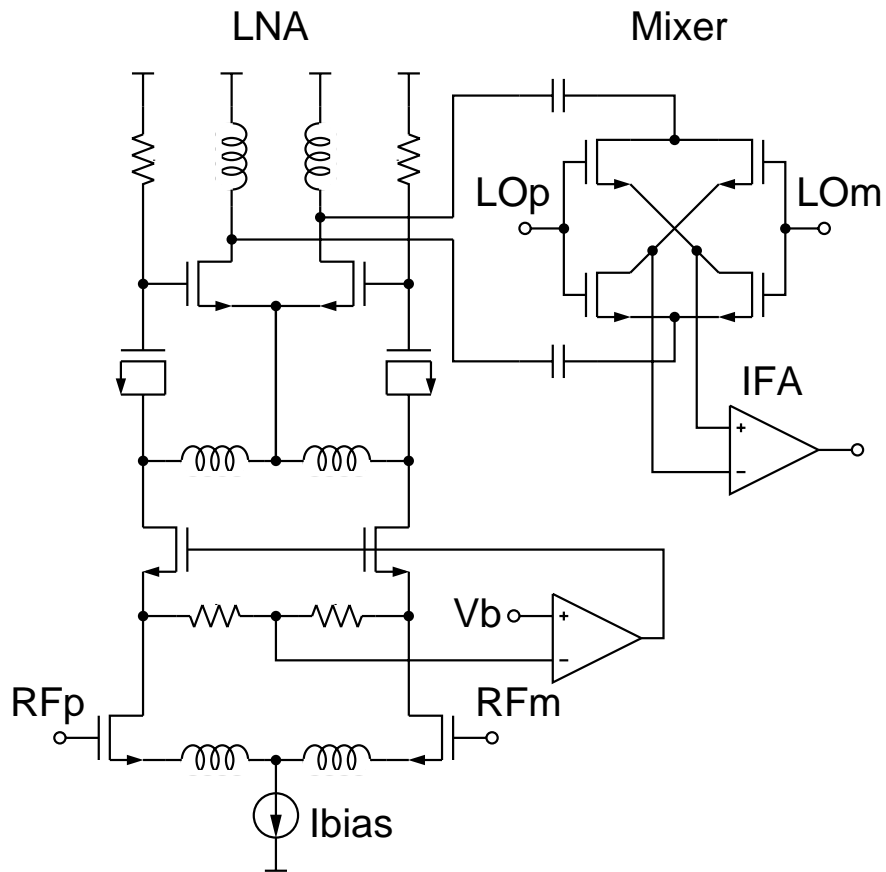
FILTER: SUMMARY

- The active filter is the dynamic-range bottleneck.
 - Noise figure is independent of power consumption.
 - Minimize the filter impedance level to increase dynamic range.
 - Minimize the order and Q of the filter.
- Transconductor architecture figure of merit Γ_m .
 - Power-efficiency, β .
 - Noise factor, ϵ .
 - Linearity, V_{IP3} .
- Results: 60dB SFDR, 10mW power consumption, enabled by new transconductor architecture.

OUTLINE

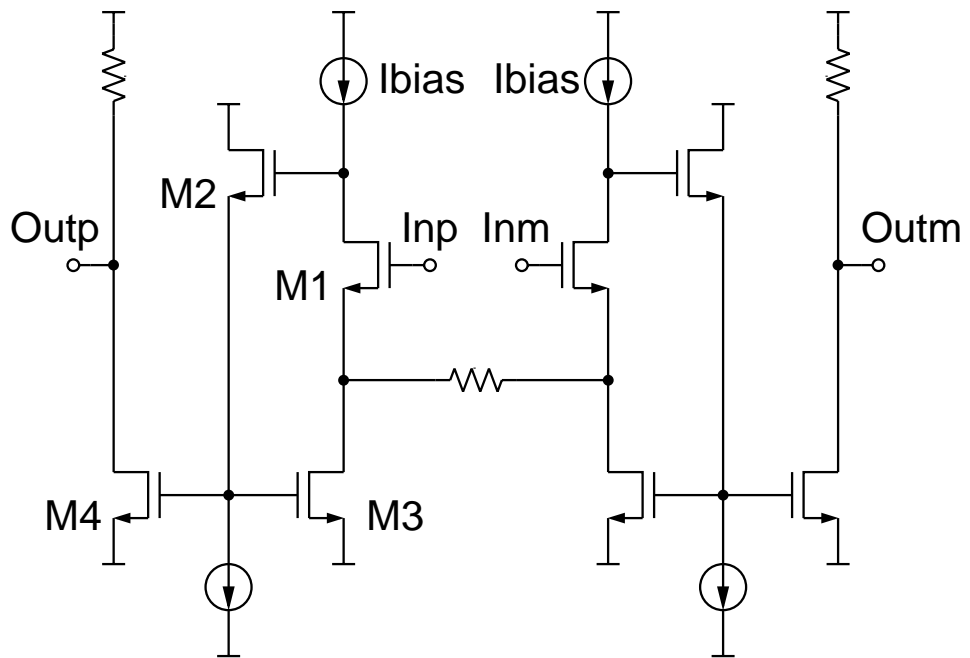
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IMPLEMENTATION: LNA / MIXER

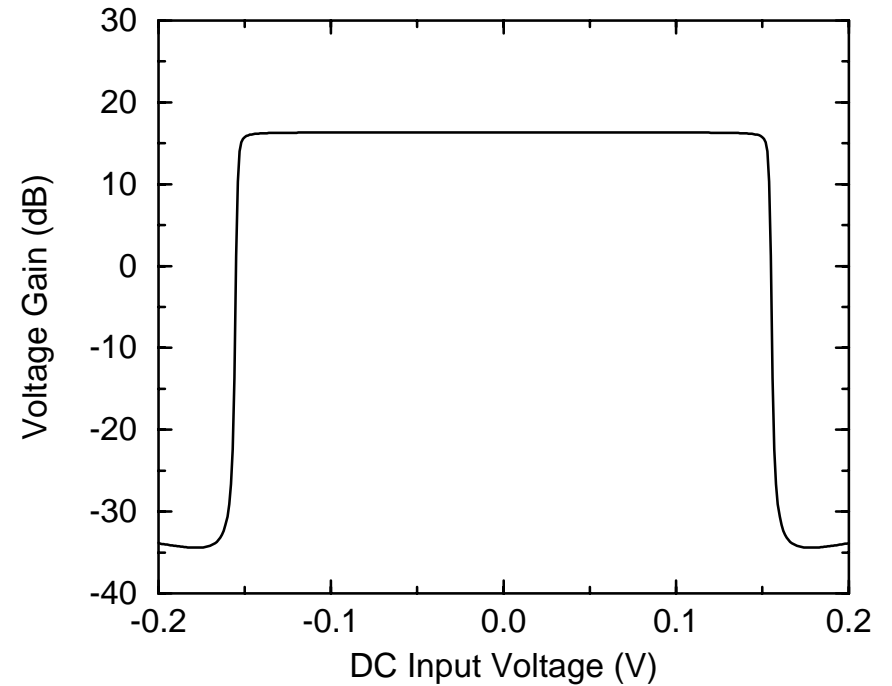


Shahani, Shaeffer and Lee, "A 12mW Wide Dynamic Range CMOS GPS Receiver", ISSCC 97

IMPLEMENTATION: IFA

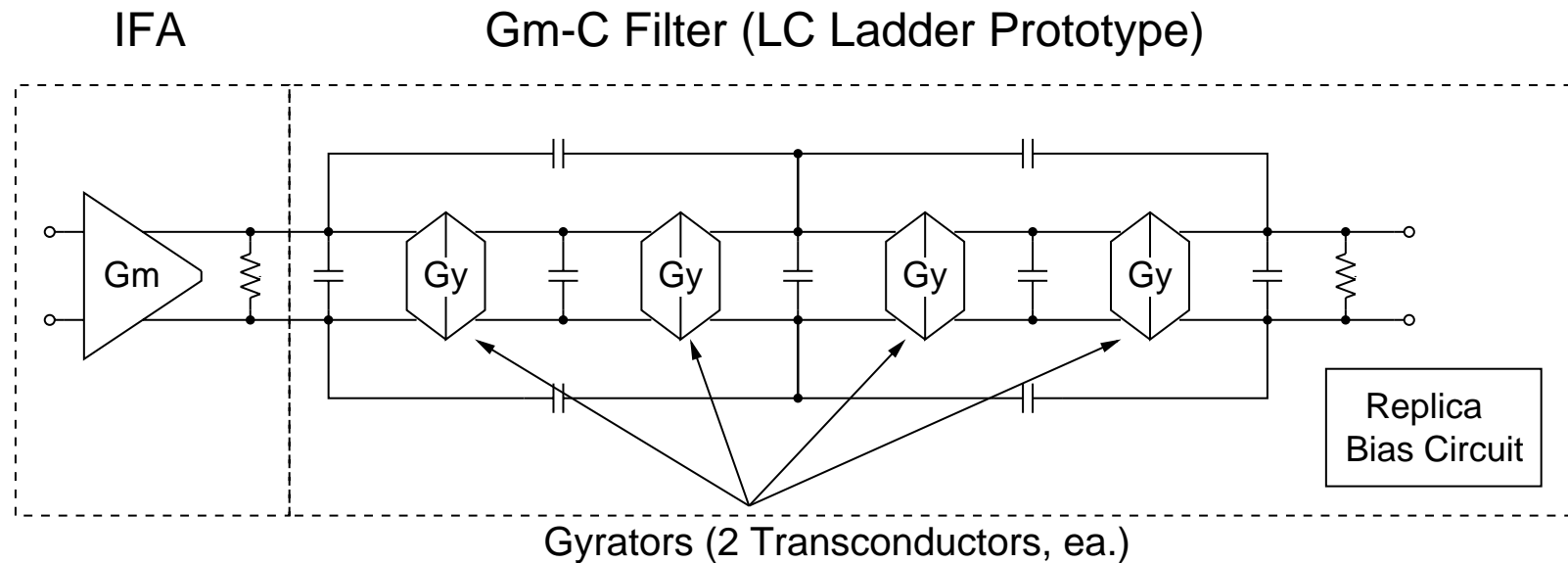


Simulated IFA Voltage Gain



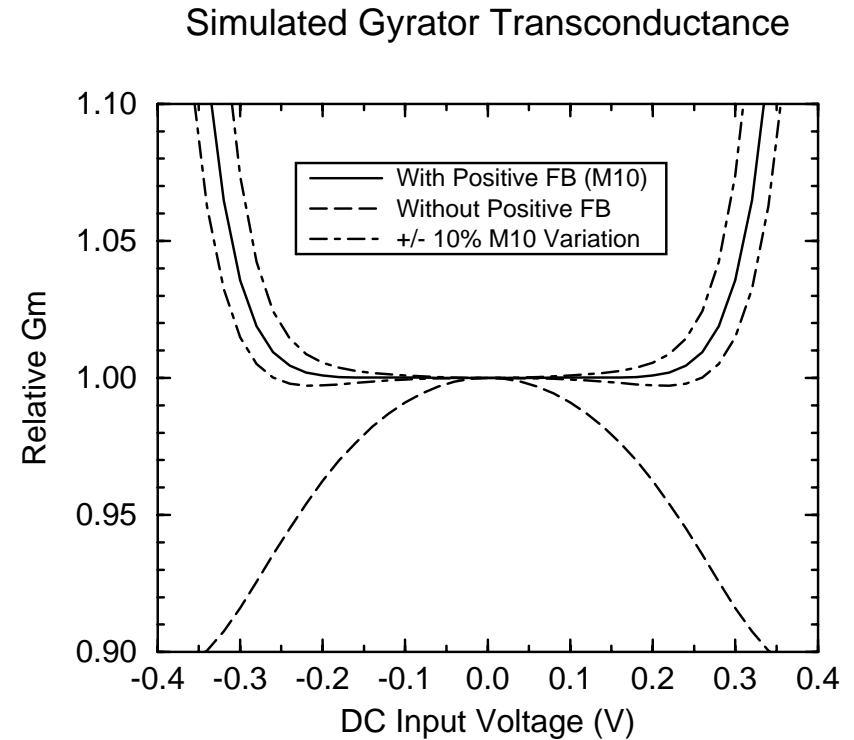
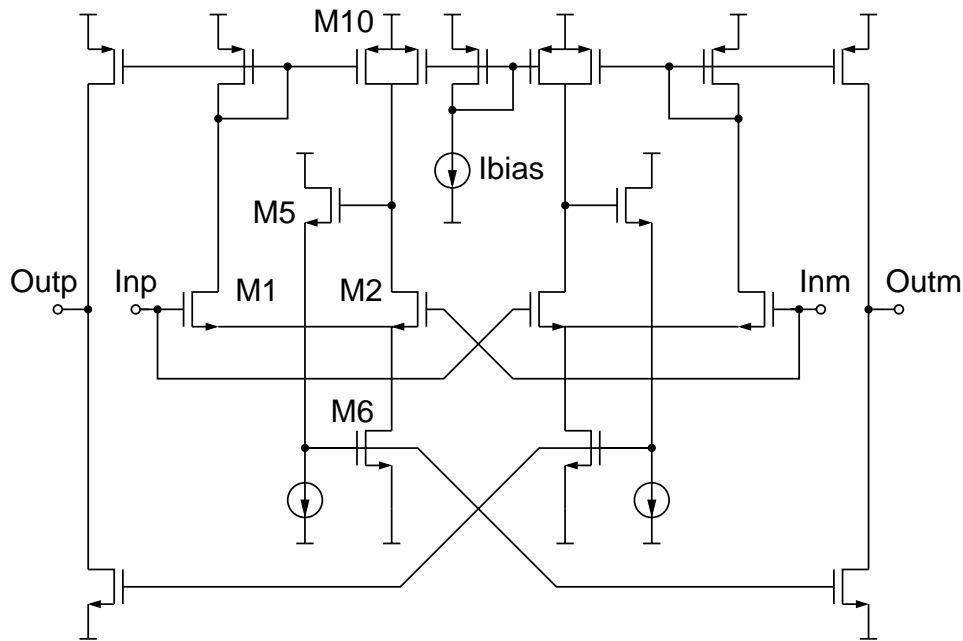
- Low input capacitance, high linearity.
- Load resistors terminate the active filter input.

IMPLEMENTATION: GM-C FILTER ARCHITECTURE



- Design based on a 5th-order LC elliptical prototype.
- The dynamic-range limiting block in the system.

IMPLEMENTATION: GM-C FILTER TRANSCONDUCTOR



Use two *square-law* transconductors to build a *linear*, class-AB transconductor. A little positive feedback (M10) compensates for mobility degradation in M1.

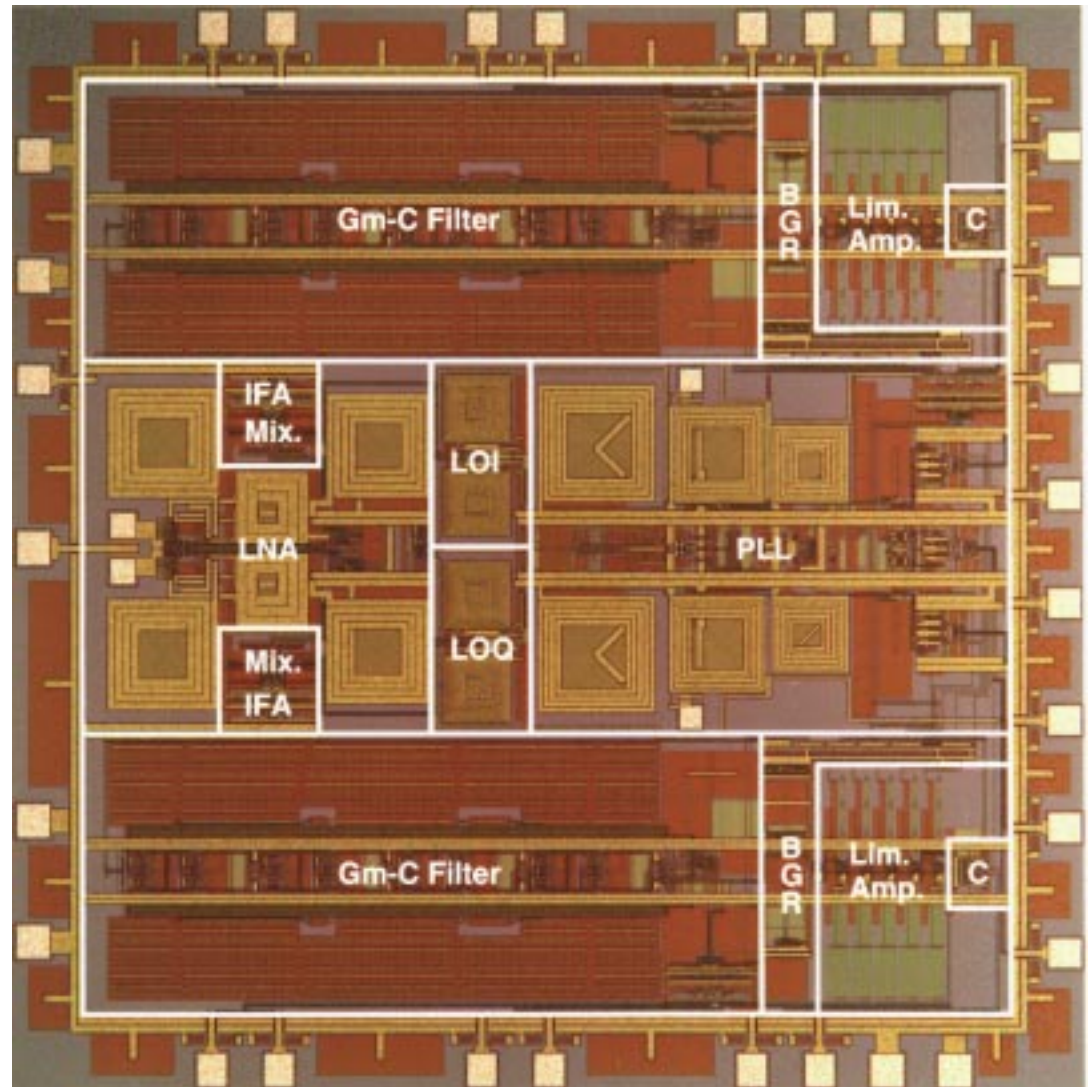
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EXPERIMENTAL RESULTS: DIE PHOTO

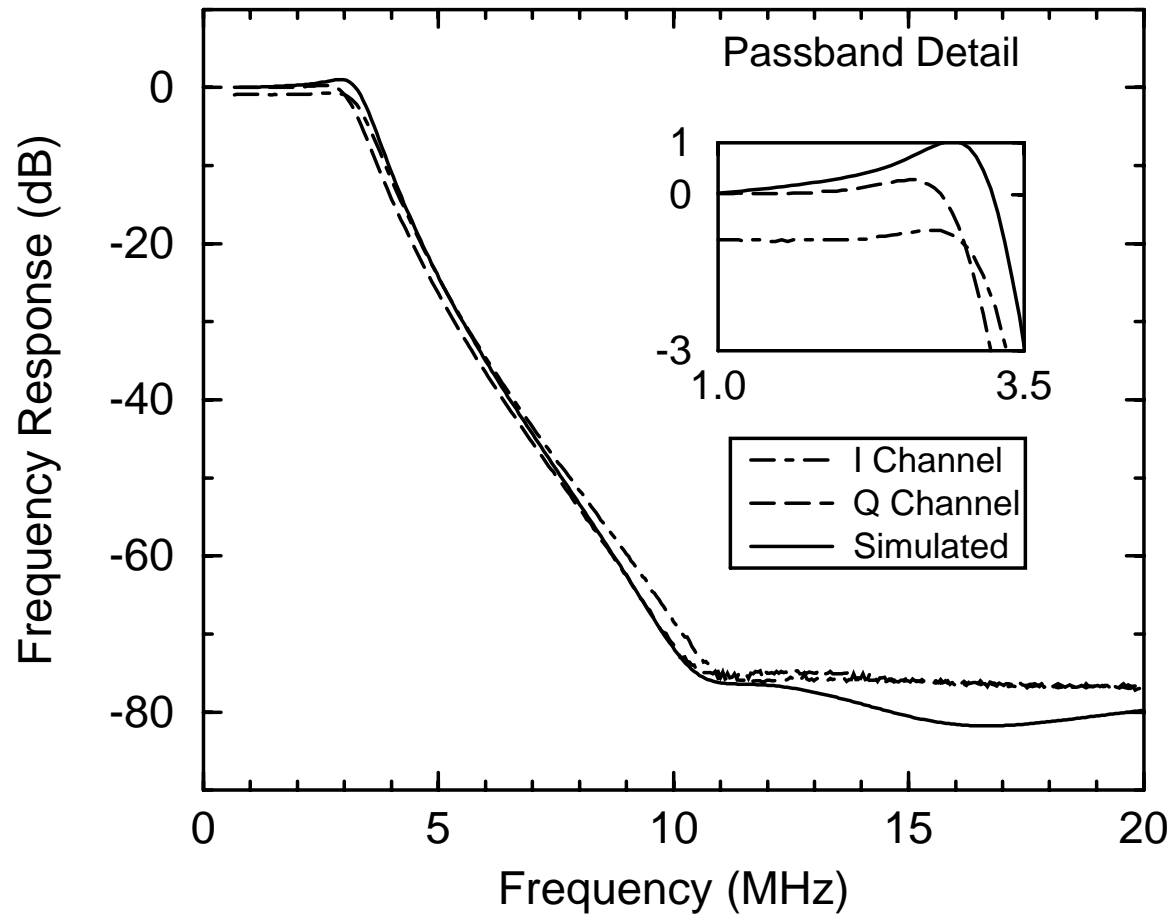
A 115mW CMOS GPS receiver

- 11.2mm² die area.
- 0.5μm CMOS technology.
- Polysilicon salicide block.
- Metal/poly capacitors.
- 16 spiral inductors w/
patterned ground shields.
Avg. # turns = 5.5
- 1.2nF on-chip supply
decoupling cap.

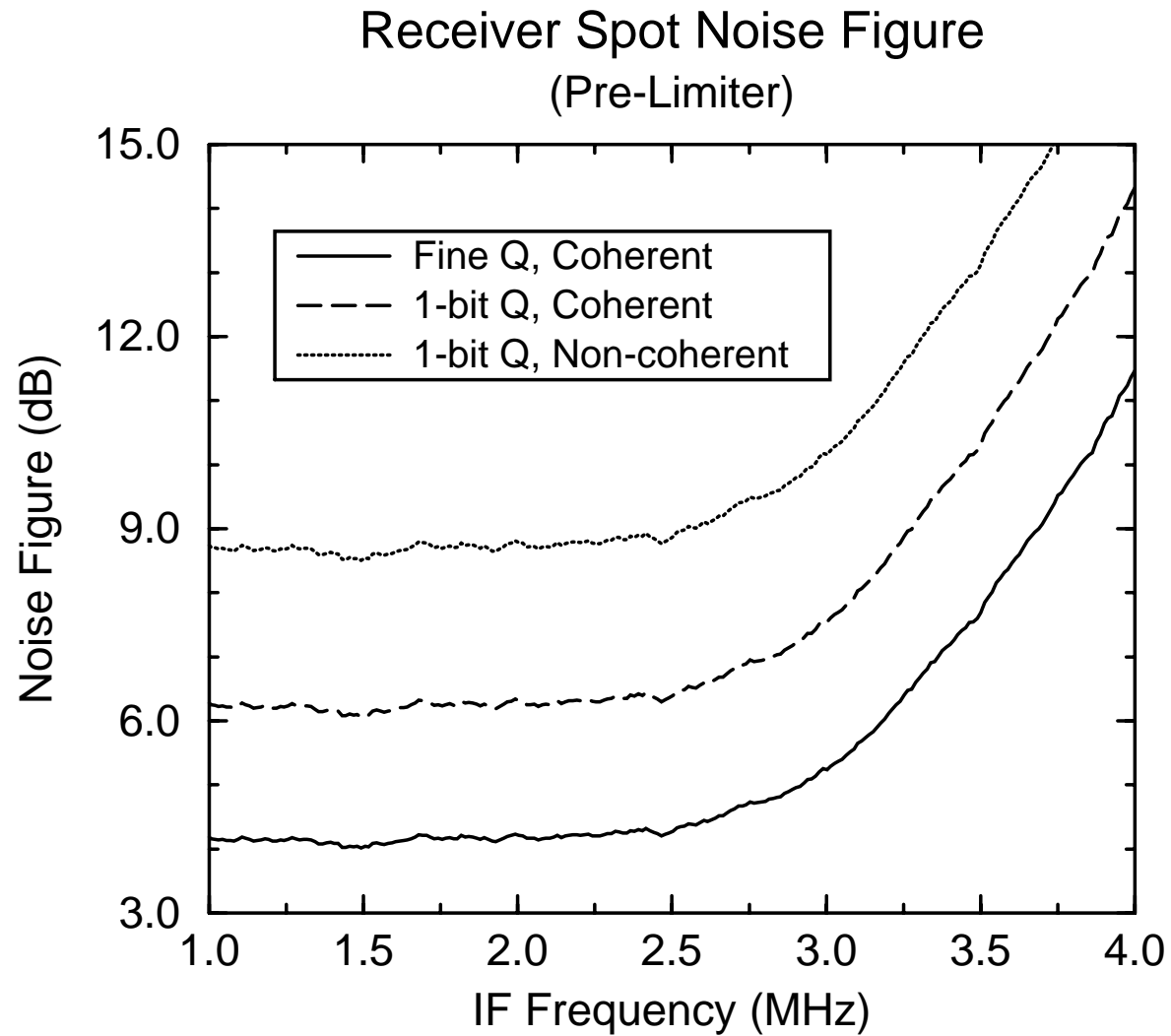


EXPERIMENTAL RESULTS: FREQUENCY RESPONSE

Signal Path Frequency Response

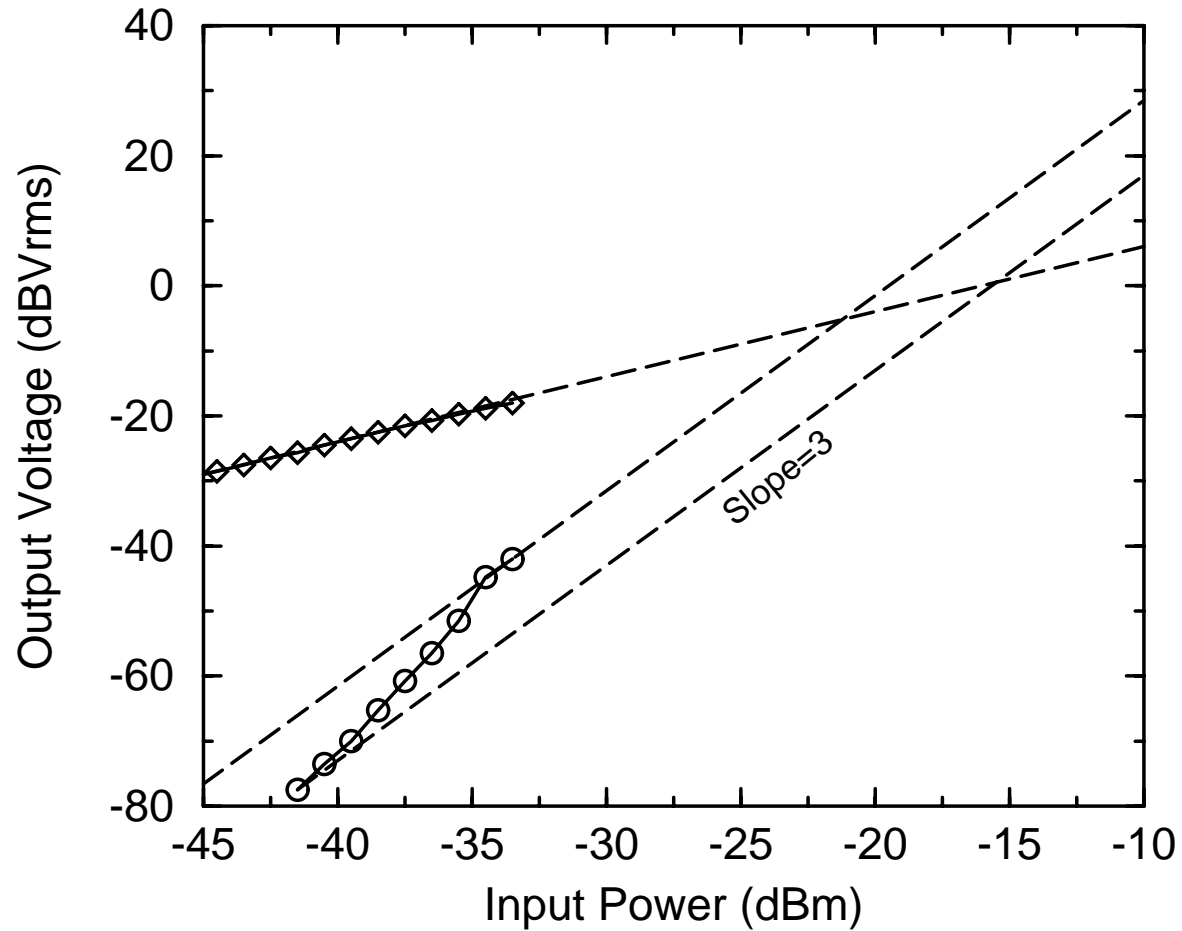


EXPERIMENTAL RESULTS: NOISE FIGURE



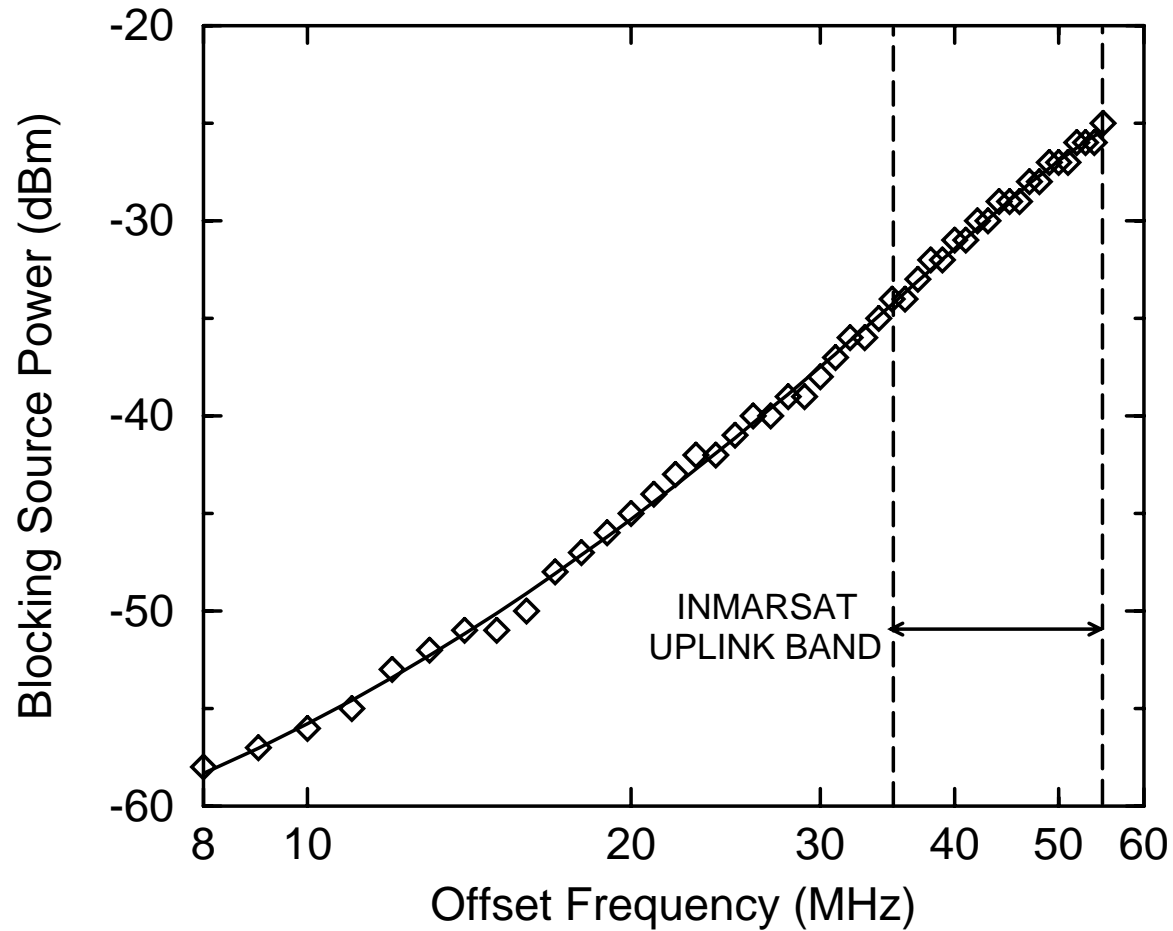
EXPERIMENTAL RESULTS: LINEARITY

Signal Path 3rd Order Intermodulation



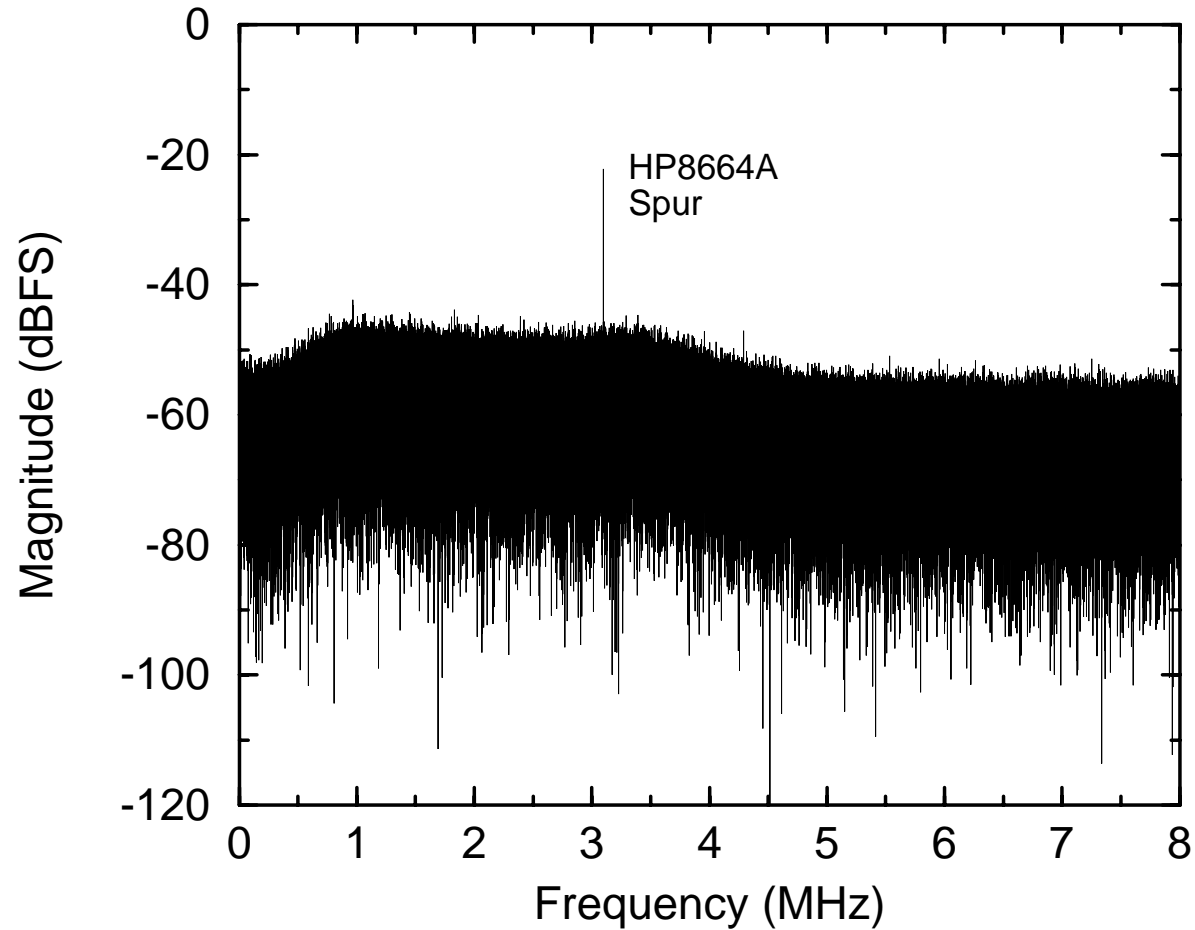
EXPERIMENTAL RESULTS: BLOCKING PERFORMANCE

Receiver 1-dB Blocking De-Sensitization
(No Front-End RF Filter)



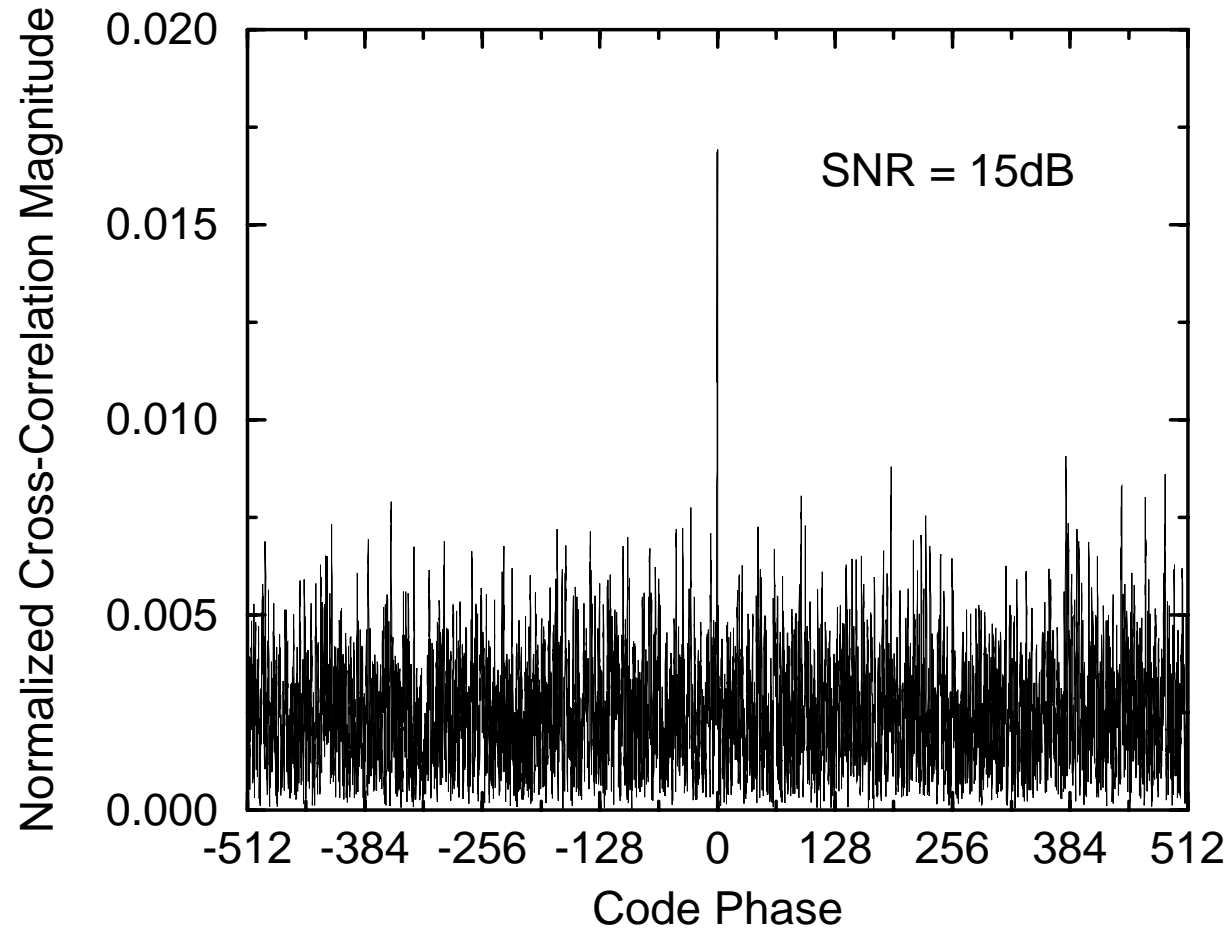
EXPERIMENTAL RESULTS: 1-BIT OUTPUT SPECTRUM

Receiver Output Spectrum
(Pre-Correlation)



EXPERIMENTAL RESULTS: CODE CORRELATION

Non-Coherent Receiver Output
Gold Code Cross-Correlation



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PERFORMANCE SUMMARY

<i>Signal Path Performance</i>		<i>PLL Performance</i>	
LNA Noise Figure	2.4dB	Loop Bandwidth	5MHz
LNA S11	$\leq -15\text{dB}$	Spurious Tones	$\leq -42\text{dBc}$
Coherent Receiver NF	4.1dB	VCO Tuning Range	240MHz ($\pm 7.6\%$)
IIP3 (Filter-limited)	-16dBm @ -43dBm P_s	VCO Gain Constant	240MHz/V
Peak SFDR	60dB	LO Leakage @ LNA	$< -53\text{dBm}$
Filter Cutoff Freq.	3.5MHz		
Filter PB Peaking	$\leq 1\text{dB}$	<i>Power/Technology</i>	
Filter SB Atten.	$\geq 52\text{dB}$ @ 8MHz $\geq 68\text{dB}$ @ 10MHz	Signal Path	79mW
		PLL / VCO	36mW
Pre-Filter G_p	19dB	Supply Voltage	2.5V
Pre-Filter A_v	32dB		
Total G_p	$\approx 94\text{dB}$	Die Area	11.2mm ²
Total A_v	$\approx 122\text{dB}$	Technology	0.5 μm CMOS
Non-Coherent Output SNR	15dB		

CONTRIBUTIONS

- CMOS LNAs:
 - Theoretical investigation of induced gate noise.
 - Power-constrained noise figure optimization technique.
 - CMOS LNA with 2.4dB noise figure at 1.6GHz on 12mW P_D .
- CMOS Active Filters:
 - Theoretical SFDR investigation, transconductor F.O.M., Γ_m .
 - New transconductor architecture with high Γ_m .
 - CMOS filter with 60dB SFDR at 3MHz on 10mW P_D .
- First CMOS GPS Receiver:
 - Developed a new GPS receiver architecture.
 - High performance, highly integrated, low P_D of 115mW.

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Ernie McReynolds

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